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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK3419

Silicon N Channel MOS FET
High Speed Power Switching

RENESAS

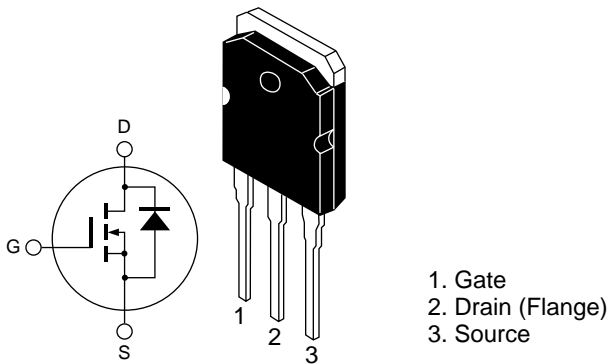
ADE-208-942 (Z)
1st. Edition
Mar. 2001

Features

- Low on-resistance
 $R_{DS(on)} = 4.3 \text{ m}\Omega$ typ.
- 4 V gate drive device
- High speed switching

Outline

TO-3P



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	90	A
Drain peak current	$I_{D (pulse)}$ ^{Note 1}	360	A
Body-drain diode reverse drain current	I_{DR}	90	A
Avalanche current	I_{AP} ^{Note 3}	65	A
Avalanche energy	E_{AR} ^{Note 3}	362	mJ
Channel dissipation	P_{ch} ^{Note 2}	150	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ C$

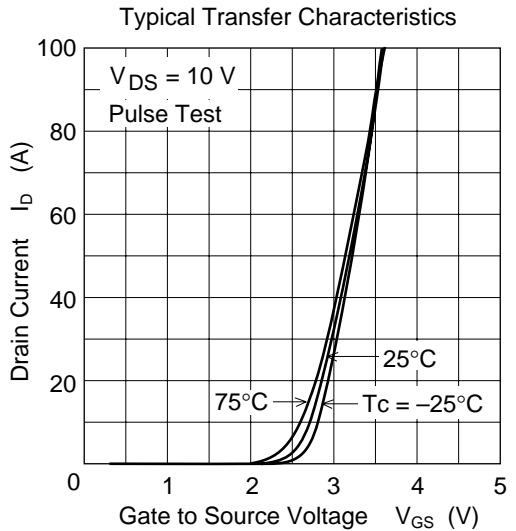
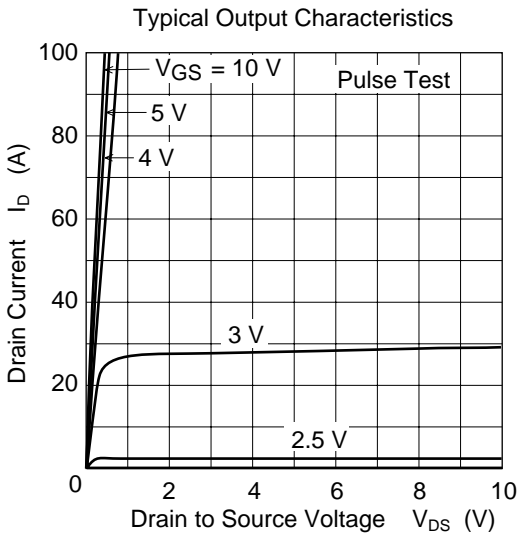
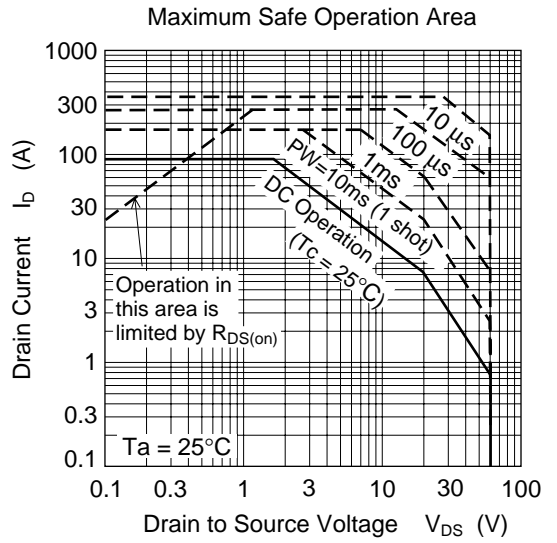
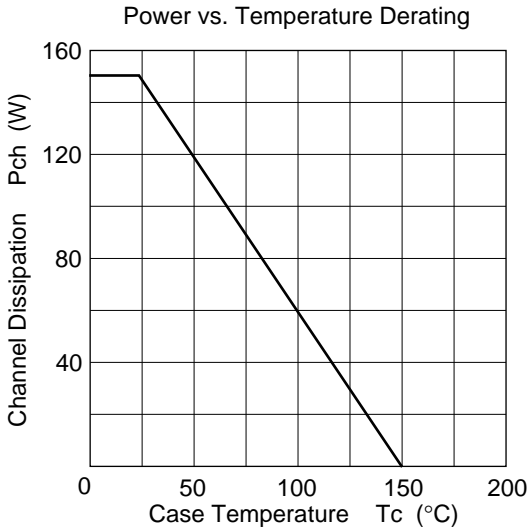
3. Value at $T_{ch} = 25^\circ C$: $R_g \geq 50 \Omega$

Electrical Characteristics (Ta = 25°C)

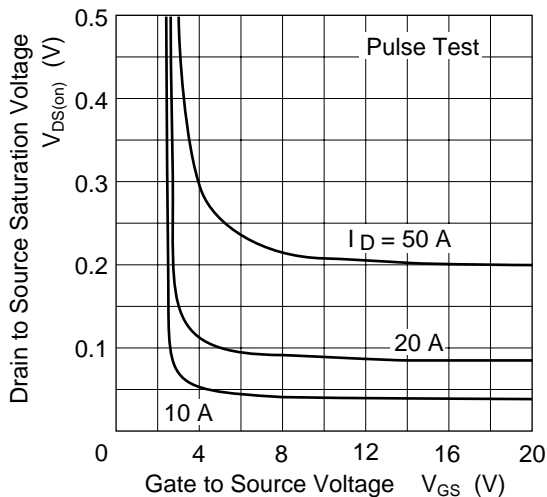
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I_{DSS}	—	—	10	μA	$V_{DS} = 60 \text{ V}, V_{GS} = 0$
Zero Gate voltage drain drain current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$ ^{Note 1}
Forward transfer admittance	$ y_{fs} $	55	90	—	S	$I_D = 45 \text{ A}, V_{DS} = 10 \text{ V}$ ^{Note 1}
Static drain to source on state resistance	$R_{DS(on)}$	—	4.3	5.5	$\text{m}\Omega$	$I_D = 45 \text{ A}, V_{GS} = 10 \text{ V}$ ^{Note 1}
	$R_{DS(on)}$	—	6.0	9.0	$\text{m}\Omega$	$I_D = 45 \text{ A}, V_{GS} = 4 \text{ V}$ ^{Note 1}
Input capacitance	C_{iss}	—	9770	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	1340	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	470	—	pF	$f = 1 \text{ MHz}$
Total gate charge	Q_g	—	180	—	nc	$V_{DD} = 50 \text{ V}$
Gate to source charge	Q_{gs}	—	32	—	nc	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	36	—	nc	$I_D = 90 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	53	—	ns	$V_{GS} = 10 \text{ V}$
Rise time	t_r	—	320	—	ns	$I_D = 45 \text{ A}$
Turn-off delay time	$t_{d(off)}$	—	700	—	ns	$R_L = 0.67 \Omega$
Fall time	t_f	—	380	—	ns	
Body-drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 90 \text{ A}, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	75	—	ns	$I_F = 90 \text{ A}, V_{GS} = 0$ $diF/dt = 50 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

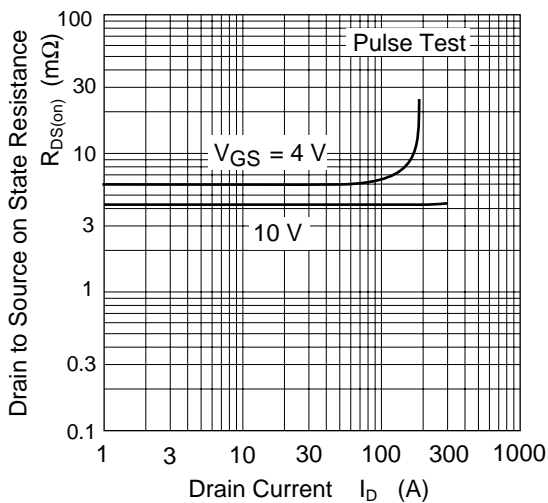
Main Characteristics



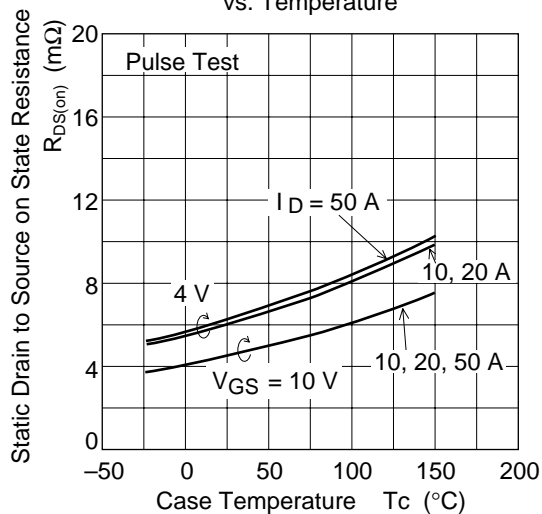
Drain to Source Saturation Voltage vs. Gate to Source Voltage



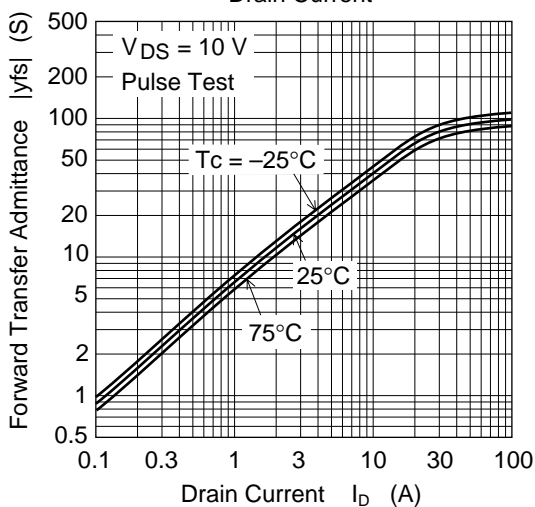
Static Drain to Source on State Resistance vs. Drain Current



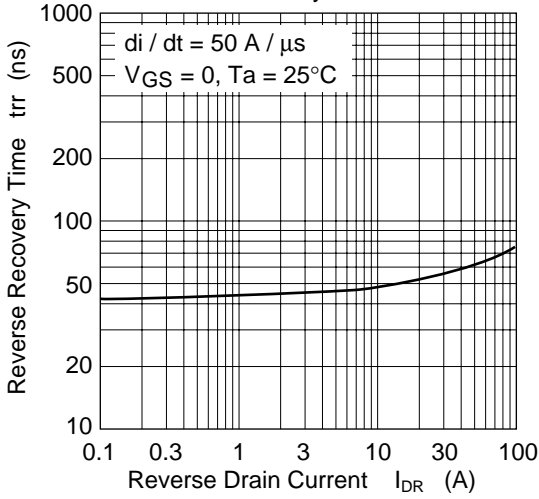
Static Drain to Source on State Resistance vs. Temperature



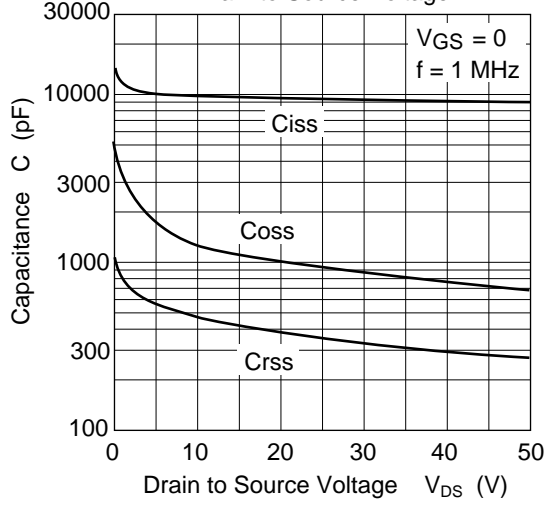
Forward Transfer Admittance vs. Drain Current



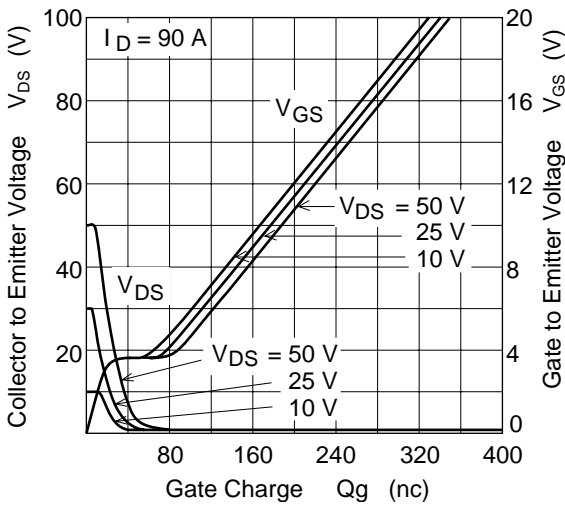
Body-Drain Diode Reverse Recovery Time



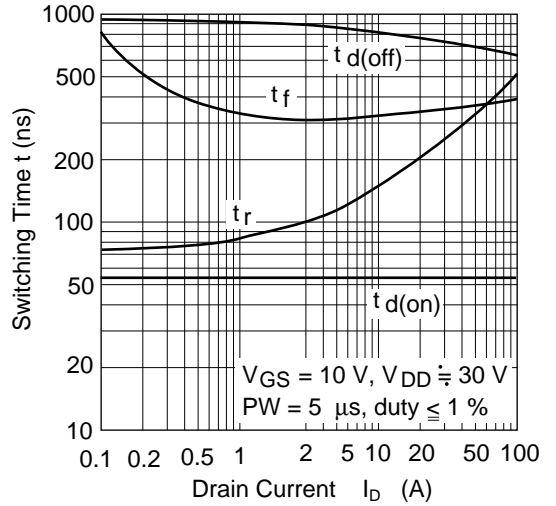
Typical Capacitance vs. Drain to Source Voltage

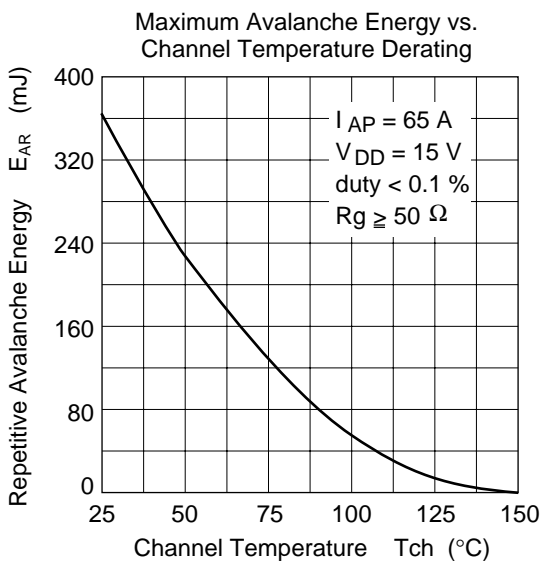
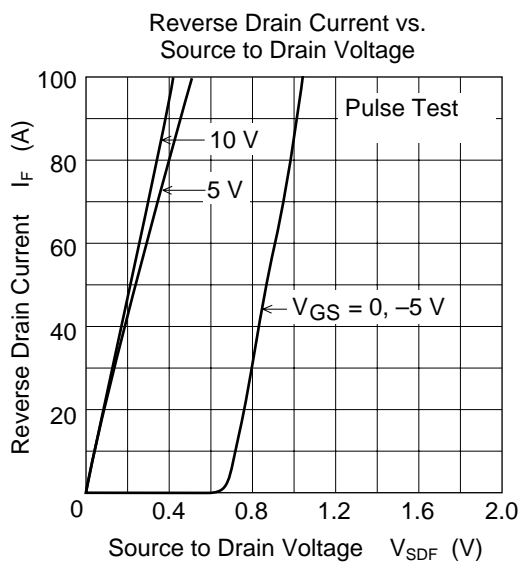


Dynamic Input Characteristics

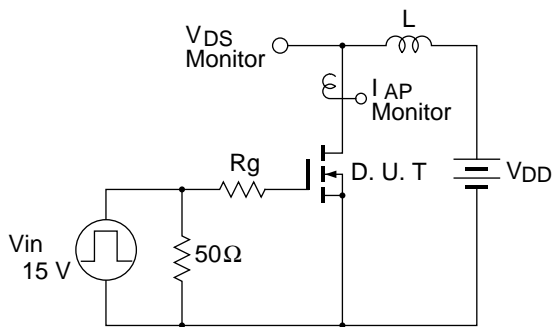


Switching Characteristics



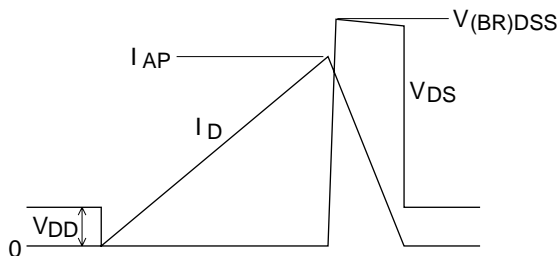


Avalanche Test Circuit



Avalanche Waveform

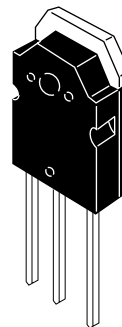
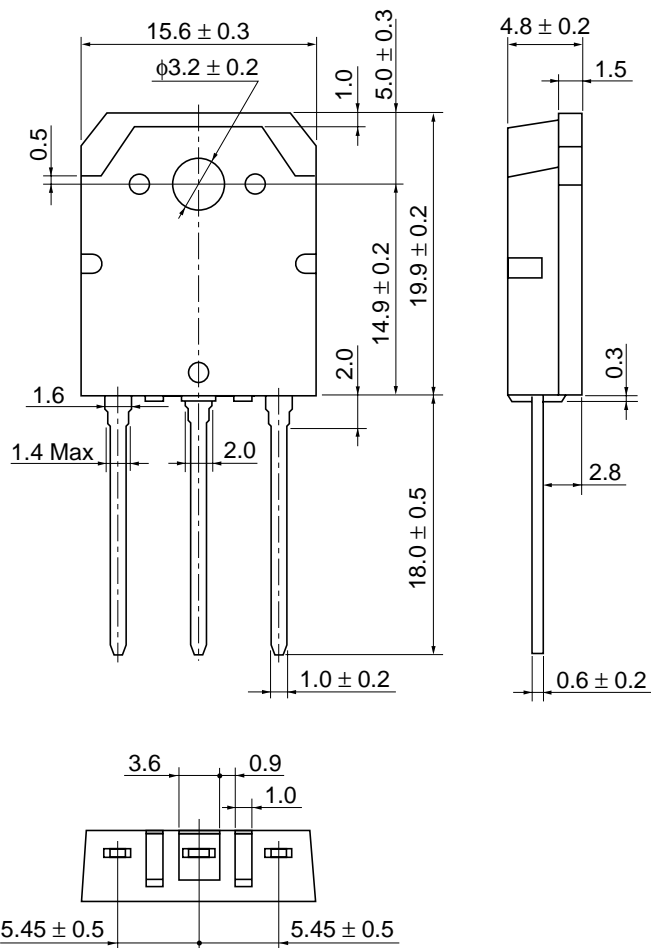
$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

Cautions

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Colophon 2.0



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